

Dual General Purpose Transistors

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

- Device Marking:
 LBC856BDW1T1 = 3B
 LBC857BDW1T1 = 3F
 LBC857CDW1T1 = 3G
 LBC858BDW1T1 = 3K
 LBC858CDW1T1 = 3L

MAXIMUM RATINGS

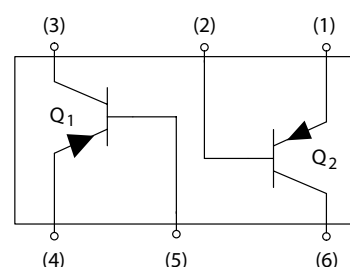
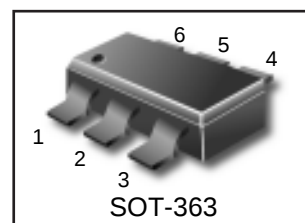
Rating	Symbol	BC856	BC857	BC858	Unit
Collector-Emitter Voltage	V_{CEO}	-65	-45	-30	V
Collector-Base Voltage	V_{CBO}	-80	-50	-30	V
Emitter-Base Voltage	V_{EBO}	-5.0	-5.0	-5.0	V
Collector Current – Continuous	I_C	-100	-100	-100	mAdc

THERMAL CHARACTERISTICS

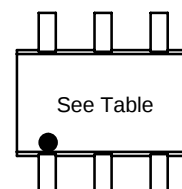
Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1.) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	380 250 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in

LBC856*DW1T1



DEVICE MARKING



ORDERING INFORMATION

Device	Package	Shipping
LBC856BDW1T1	SOT-363	3000 Units/Reel
LBC857BDW1T1	SOT-363	3000 Units/Reel
LBC857CDW1T1	SOT-36 3	3000 Units/Reel
LBC858BDW1T1	SOT-363	3000 Units/Reel
LBC858CDW1T1	SOT-363	3000 Units/Reel

LBC856BDW1T1, LBC857BDW1T1, LBC857CDW1T1, LBC858BDW1T1, LBC858CDW1T1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$) LBC856 Series LBC857 Series LBC858 Series	$V_{(BR)CEO}$	-65 -45 -30	– – –	– – –	V
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$) LBC856 Series LBC857 Series LBC858 Series	$V_{(BR)CES}$	-80 -50 -30	– – –	– – –	V
Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$) LBC856 Series LBC857 Series LBC858 Series	$V_{(BR)CBO}$	-80 -50 -30	– – –	– – –	V
Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$) LBC856 Series LBC857 Series LBC858 Series	$V_{(BR)EBO}$	-5.0 -5.0 -5.0	– – –	– – –	V
Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	– –	– –	-15 -4.0	nA μA

ON CHARACTERISTICS

DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) LBC856B, LBC857B, LBC858B LBC857C, LBC858C ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) LBC856B, LBC857B, LBC858B LBC857C, LBC858C	h_{FE}	– – 220 420	150 270 290 520	– – 475 800	–
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{CE(sat)}$	– –	– –	-0.3 -0.65	V
Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{BE(sat)}$	– –	-0.7 -0.9	– –	V
Base–Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	$V_{BE(on)}$	-0.6 –	– –	-0.75 -0.82	V

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{ob}	–	–	4.5	pF
Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	–	–	10	dB

LBC856BDW1T1, LBC857BDW1T1, LBC857CDW1T1, LBC858BDW1T1, LBC858CDW1T1

TYPICAL CHARACTERISTICS – LBC856

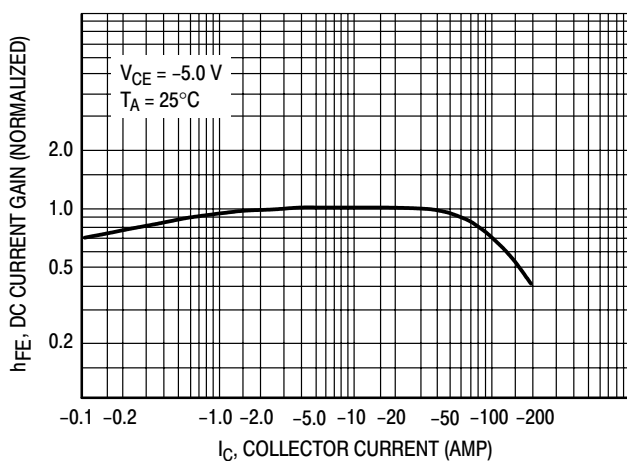


Figure 1. DC Current Gain

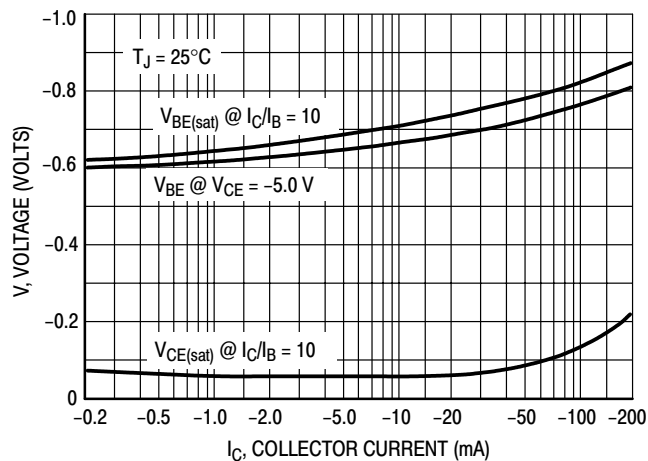


Figure 2. "On" Voltage

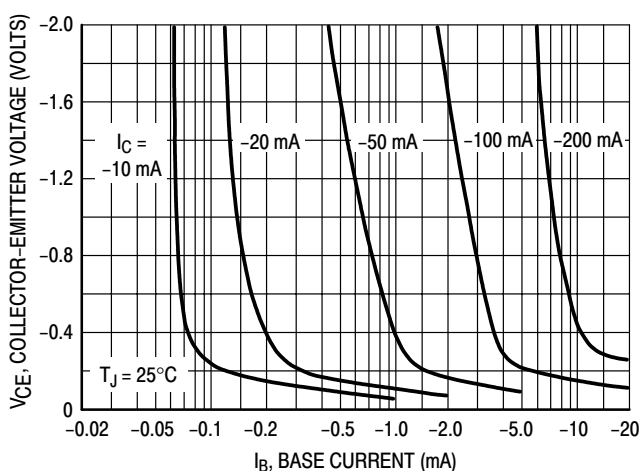


Figure 3. Collector Saturation Region

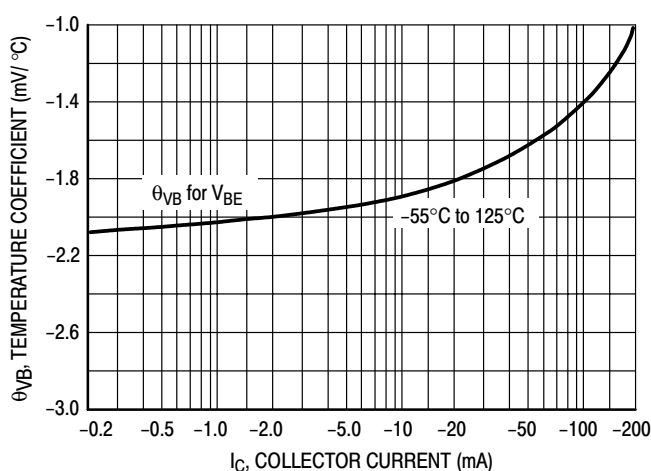


Figure 4. Base-Emitter Temperature Coefficient

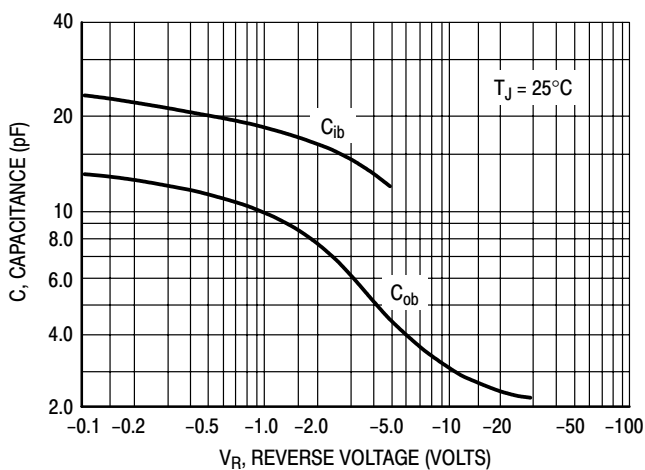


Figure 5. Capacitance

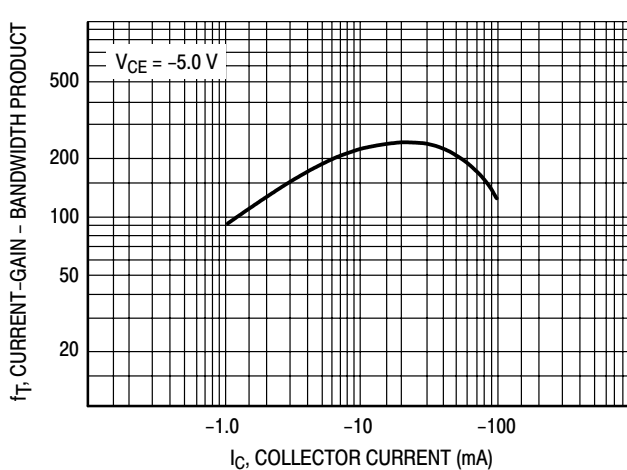


Figure 6. Current-Gain – Bandwidth Product

LBC856BDW1T1, LBC857BDW1T1, LBC857CDW1T1, LBC858BDW1T1, LBC858CDW1T1

TYPICAL CHARACTERISTICS – LBC857/LBC858

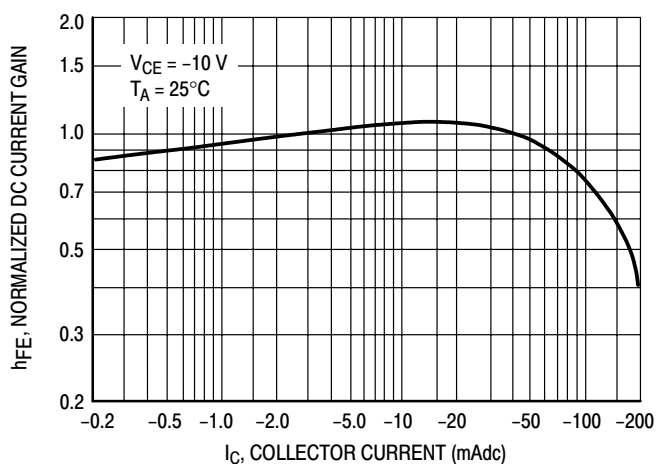


Figure 7. Normalized DC Current Gain

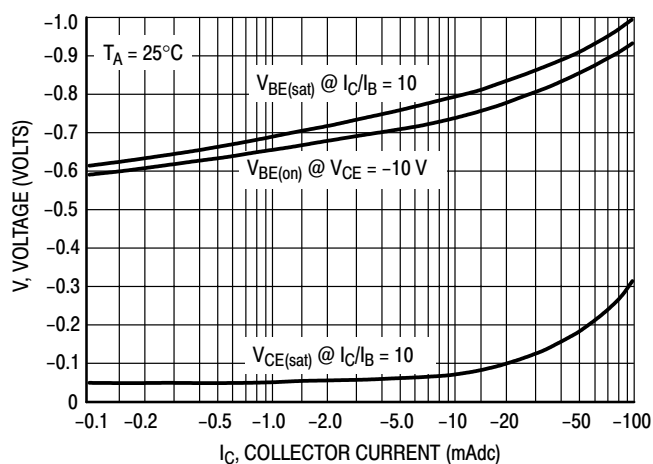


Figure 8. "Saturation" and "On" Voltages

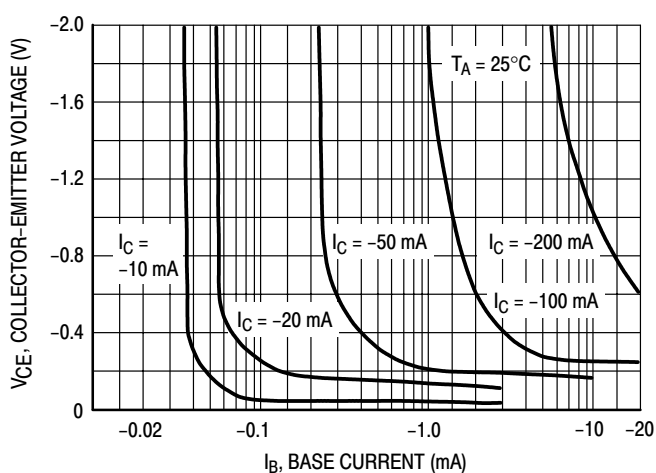


Figure 9. Collector Saturation Region

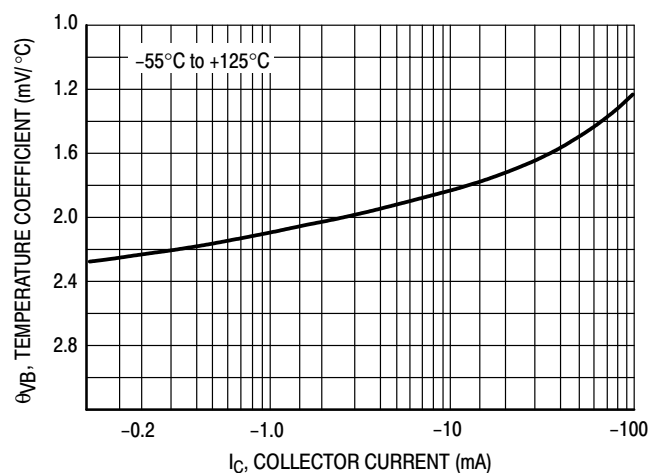


Figure 10. Base-Emitter Temperature Coefficient

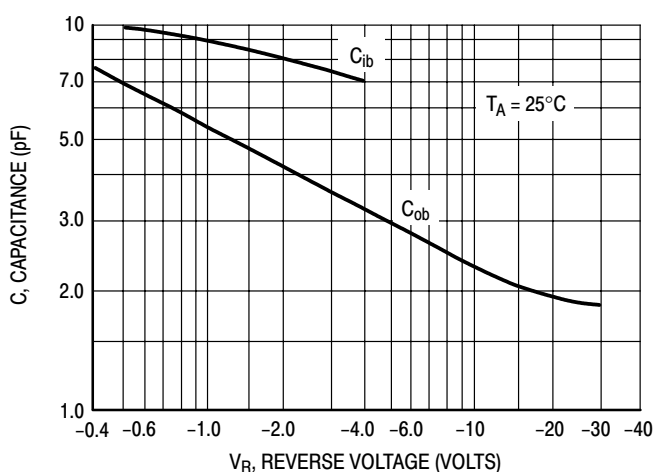


Figure 11. Capacitances

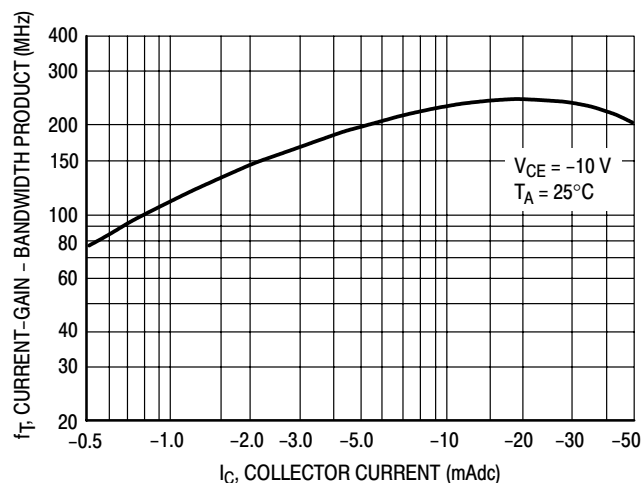


Figure 12. Current-Gain - Bandwidth Product

LBC856BDW1T1, LBC857BDW1T1, LBC857CDW1T1, LBC858BDW1T1, LBC858CDW1T1

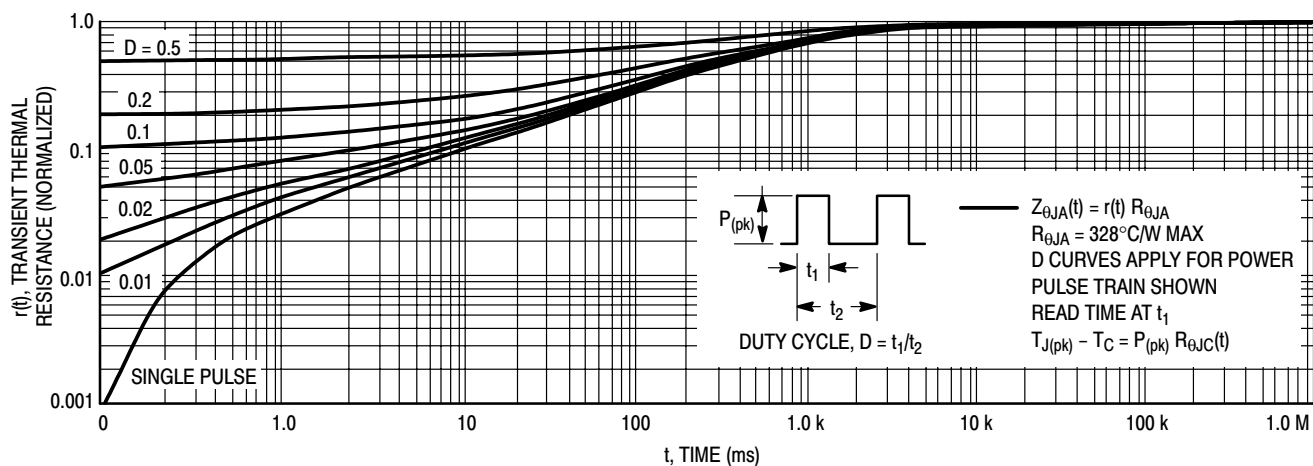


Figure 13. Thermal Response

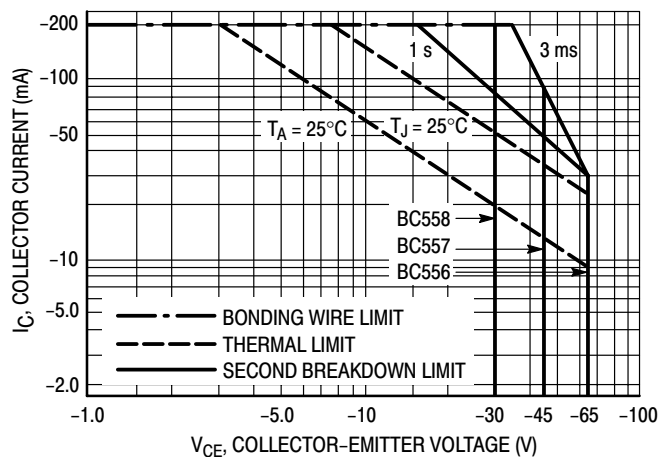


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

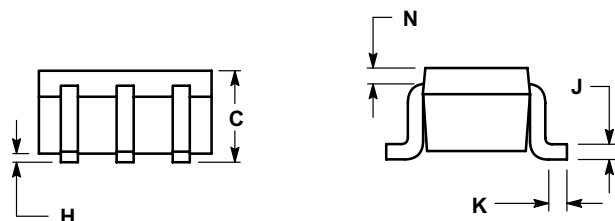
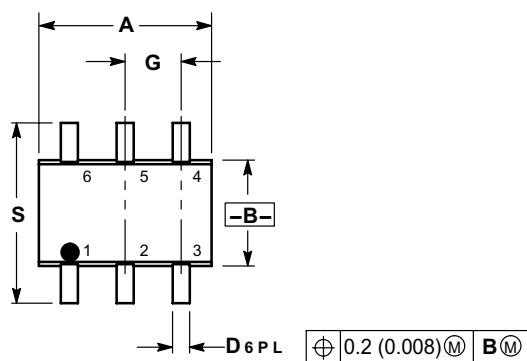
The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

LBC856BDW1T1, LBC857BDW1T1, LBC857CDW1T1, LBC858BDW1T1, LBC858CDW1T1

SC-88/SOT-363

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

- PIN 1. EMITTER 2
 2. BASE 2
 3. COLLECTOR 1
 4. EMITTER 1
 5. BASE 1
 6. COLLECTOR 2

